

## DESCRIPTION

The H11ADB series optocouplers have two channels for high density applications. The inverse parallel channel orientation is ideal for applications which require data to be transmitted and received across the isolation boundary. Each channel consists of a GaAs LED optically coupled to a silicon NPN phototransistor.

## FEATURES

- Inverse parallel channel orientation
- High isolation voltage 5300 VAC RMS-1 minute, 7500 VAC PEAK-1 minute
- High  $BV_{CEO}$  minimum 70 volts
- Two isolated channels per package
- Underwriters Laboratory (UL) recognized file #E90700

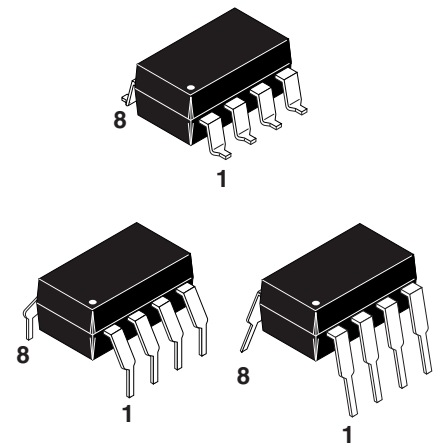
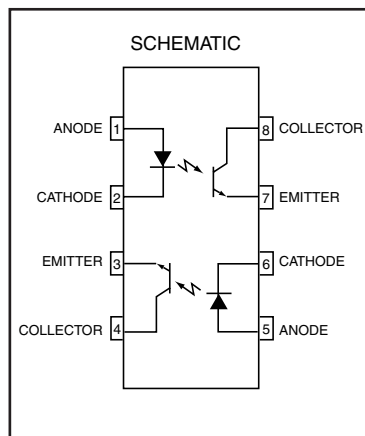
## APPLICATIONS

- AC line / Digital logic
- Digital logic / Digital logic
- Digital logic / AC Triac control

**H11ADB6**  
(CTR = 20%minimum)

**H11ADB61**  
(CTR = 50%minimum)

**H11ADB62**  
(CTR = 200%-400%)



<b>ABSOLUTE MAXIMUM RATINGS</b> (No derating required up to 85°C)			
Rating	Symbol	Value	Unit
<b>EMITTER</b> (Each channel) Forward Current - Continuous	$I_F$	60	mA
Forward Current - Peak (PW = 1µs, 300pps)	$I_{F(pk)}$	3.0	A
Reverse Voltage	$V_R$	5	V
LED Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	$P_D$	100 1.33	mW mW/°C
<b>DETECTOR</b> (Each channel) Collector Current - Continuous	$I_C$	50	mA
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	70	V
Emitter-Collector Breakdown Voltage	$BV_{ECO}$	7	V
Detector Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	$P_D$	150 2.0	mW mW/°C
<b>TOTAL DEVICE</b> Storage Temperature	$T_{STG}$	-55 to +125	°C
Operating Temperature	$T_{OPR}$	-55 to +100	°C
Lead Solder Temperature	$T_{SOL}$	260 for 10 sec	°C
Total Device Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	$P_D$	400 5.33	mW mW/°C



# PRELIMINARY 8-PIN BI-DIRECTIONAL TRANSISTOR OPTOCOUPLER

## H11ADB6, H11ADB61, H11ADB62

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C Unless otherwise specified.)

#### INDIVIDUAL COMPONENT CHARACTERISTICS

Parameter	Test Conditions	Symbol	Min	Typ**	Max	Unit
<b>EMITTER</b>						
Input Forward Voltage	(I <sub>F</sub> = 20 mA)	V <sub>F</sub>		1.2	1.5	V
Reverse Voltage	(I <sub>R</sub> = 10 μA)	V <sub>R</sub>	3.0	25		V
Reverse Current	(V <sub>R</sub> = 5 V)	I <sub>R</sub>		0.001	10	μA
Junction Capacitance	(V <sub>F</sub> = 0 V, f = 1 MHz)	C <sub>J</sub>		50		pF
<b>DETECTOR</b>						
Collector-Emitter Breakdown Voltage	(I <sub>C</sub> = 1.0 mA, I <sub>F</sub> = 0)	BV <sub>CEO</sub>	70	100		V
Emitter-Collector Breakdown Voltage	(I <sub>E</sub> = 100 μA, I <sub>F</sub> = 0)	BV <sub>ECO</sub>	7	10		V
Collector-Emitter Dark Current	(V <sub>CE</sub> = 10 V, I <sub>F</sub> = 0)	I <sub>CEO</sub>		1	100	nA
Capacitance	(V <sub>CE</sub> = 0 V, f = 1 MHz)	C <sub>CE</sub>		8		pF

#### TRANSFER CHARACTERISTICS

AC Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
<b>SWITCHING TIMES</b>						
Non-Saturated Turn-on Time	(R <sub>L</sub> = 100 Ω, I <sub>C</sub> = 2 mA, V <sub>CC</sub> = 10 V)	t <sub>on</sub>		2.4	18	μs
Non-Saturated Turn-off Time	(R <sub>L</sub> = 100 Ω, I <sub>C</sub> = 2 mA, V <sub>CC</sub> = 10 V)	t <sub>off</sub>		2.4	18	μs

#### TRANSFER CHARACTERISTICS

DC Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Current Transfer Ratio, Collector-Emitter	(I <sub>F</sub> = 5 mA, V <sub>CE</sub> = 5 V)	CTR	20			%
H11ADB6			50			
H11ADB61			200		400	
Saturation Voltage	(I <sub>F</sub> = 10 mA, I <sub>C</sub> = 2.5 mA)	V <sub>CE(sat)</sub>		0.15	0.40	V

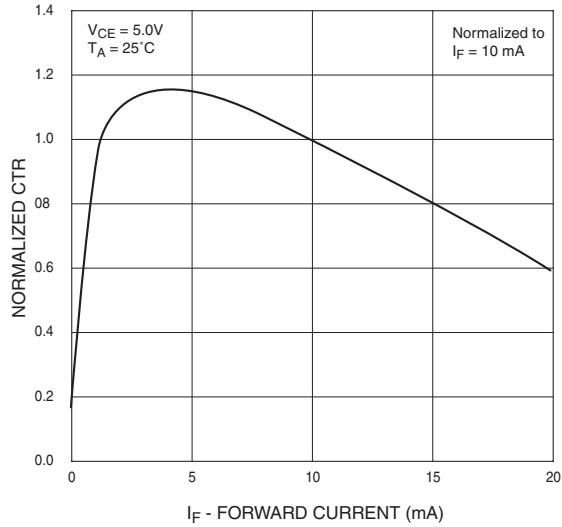
#### ISOLATION CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Min	Typ**	Max	Units
Input-Output Isolation Voltage	(I <sub>I-O</sub> ≤ 1 μA, 1 min.)	V <sub>ISO</sub>	5300			Vac(rms)
Isolation Resistance	(V <sub>I-O</sub> = 500 VDC)	R <sub>ISO</sub>	10 <sup>11</sup>			Ω
Isolation Capacitance	(f = 1 MHz)	C <sub>ISO</sub>		0.5		pf

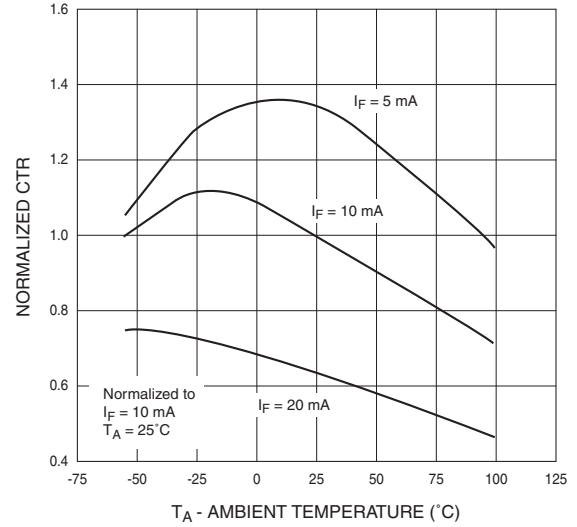
\*\* All typicals at T<sub>A</sub> = 25°C

## H11ADB6, H11ADB61, H11ADB62

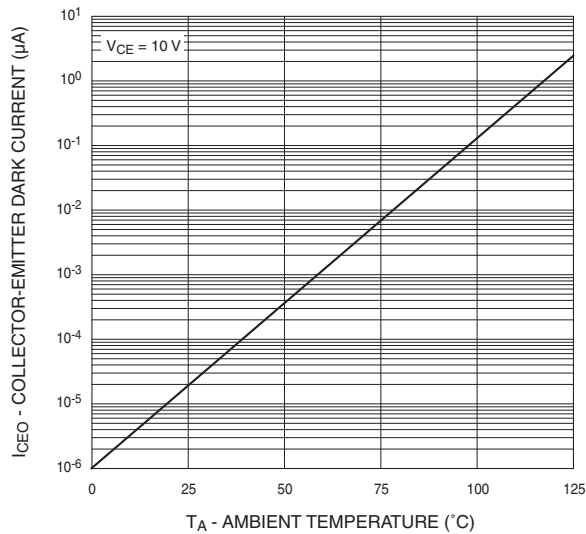
Normalized CTR vs. Forward Current



Normalized CTR vs. Ambient Temperature

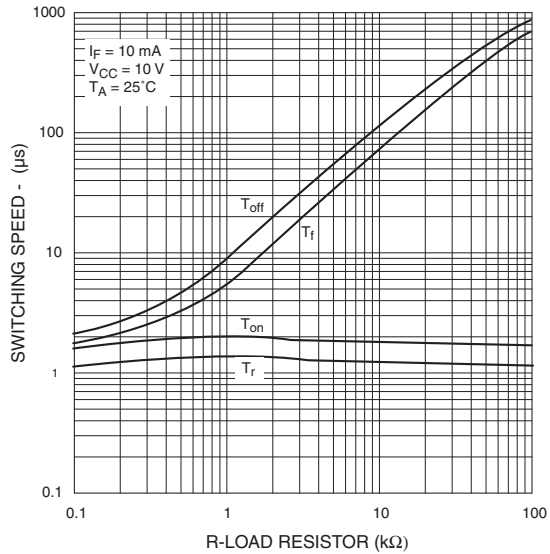


Dark Current vs. Ambient Temperature

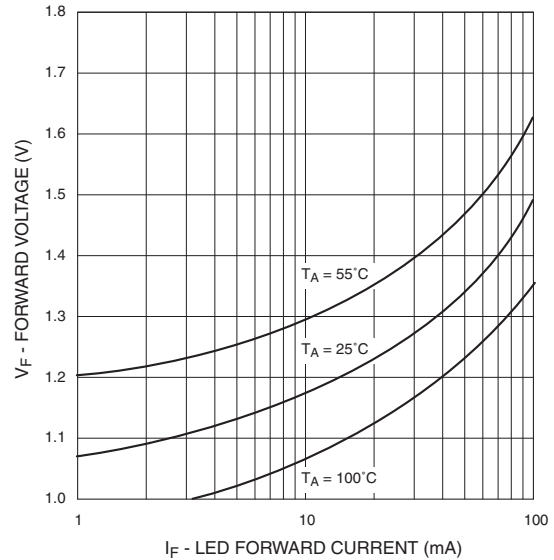


## H11ADB6, H11ADB61, H11ADB62

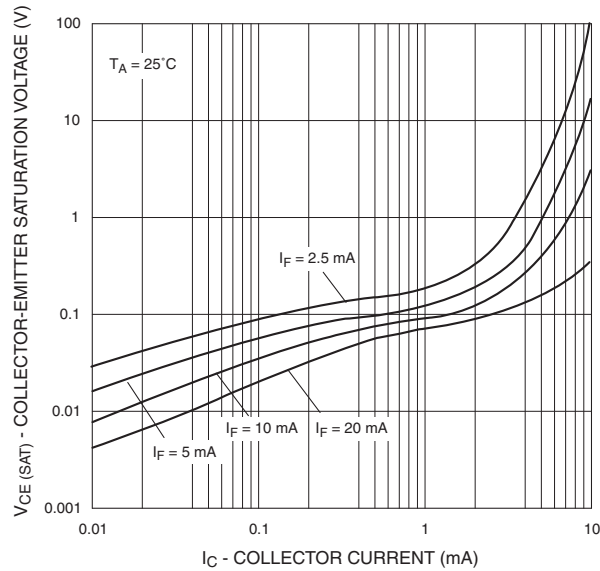
Switching Speed vs. Load Resistor



LED Forward Voltage vs. Forward Current

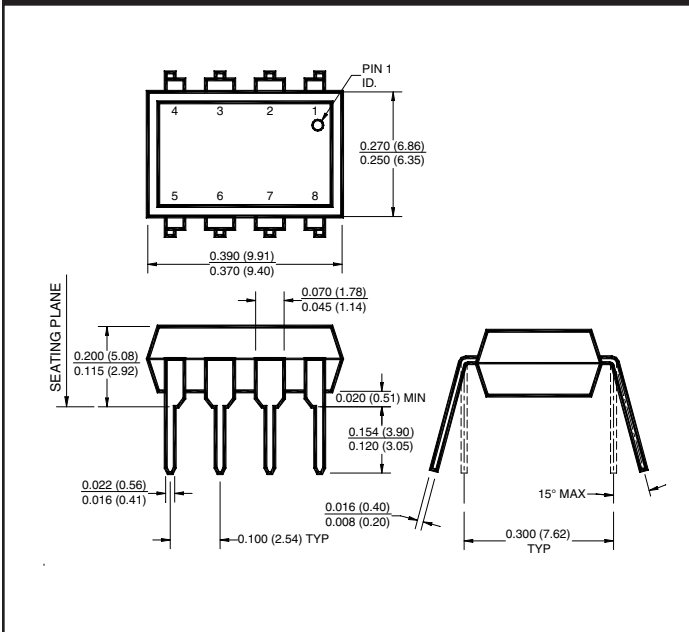


Collector-Emitter Saturation Voltage vs Collector Current

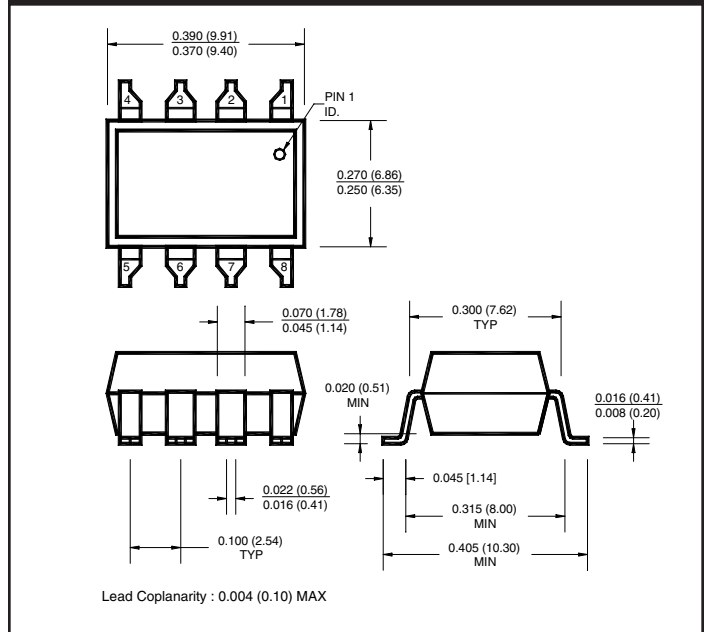


## H11ADB6, H11ADB61, H11ADB62

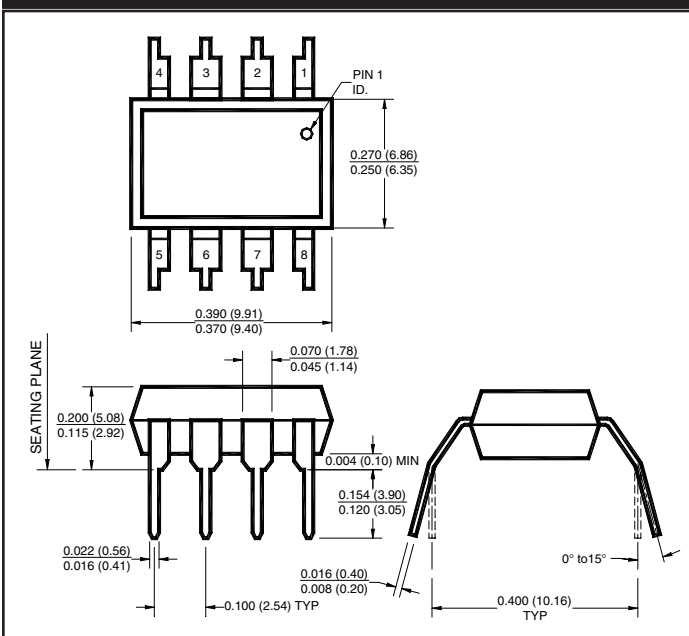
### Package Dimensions (Through Hole)



### Package Dimensions (Surface Mount)



### Package Dimensions (0.4" Lead Spacing)



#### NOTE

All dimensions are in inches (millimeters)

Call QT Optoelectronics for more information or the phone number of your nearest distributor.

United States 800-533-6786 • France 33 [0] 1.45.18.78.78 • Germany 49 [0] 89/96.30.51 • United Kingdom 44 [0] 1296 394499 • Asia/Pacific 603-7352417